

WHAT IS CLAIMED IS:

1. A semiconductor integrated circuit device comprising:
 - unit areas placed in plural form in a first direction;
 - a first line extending in the first direction over said plurality of unit areas;
 - a second line extending in the first direction along said plurality of unit areas and outside said plurality of unit areas; and
 - wiring areas provided adjacent to a first unit area of said plurality of unit areas and provided with a third line extending in a second direction, intersecting the first direction,
 - wherein said first unit area has a MOSFET formed therein,
 - wherein said third line is used to connect said second line to a terminal of said MOSFET, and
 - wherein said third line is separated from said first line electrically.
2. A semiconductor integrated circuit device comprising:
 - unit areas placed in plural form in a first direction;
 - a first line, formed with a first layer, extending in the first direction over said plurality of unit areas;
 - a second line extending in the first direction along said plurality of unit areas and outside said plurality of unit areas; and
 - wiring areas provided adjacent to a first unit area of said plurality of unit areas and provided with a third line;

wherein said first unit area has a circuit formed therein,
wherein said third line connects said second line and a terminal of said circuit,
wherein said third line is formed with a second layer which is different from
said first layer, and
wherein said third line is separated from said first line electrically.

3. A semiconductor integrated circuit device according to claim 2,
wherein said second layer is formed by a single layer.